

ABSTRACT OF THE DISCLOSURE

A low reflective film is formed of, in sequence from a side in contact with a laser chip, a first dielectric film of a refractive index n_1 and a thickness d_1 , a second dielectric film of a refractive index n_2 and a thickness d_2 , a third dielectric film of a refractive index n_3 and a thickness d_3 , and a fourth dielectric film of a refractive index n_4 and a thickness d_4 , specifically, aluminum oxide Al_2O_3 with a refractive index $n_1 = 1.638$ is used for the first dielectric film, silicon oxide SiO_2 with a refractive index $n_2 = n_4 = 1.489$ for the second and fourth dielectric films, tantalum oxide Ta_2O_5 with a refractive index $n_3 = 2.063$ for the third dielectric film, respectively, resulting in a semiconductor laser device with a reflectance which is stably controllable.